

ADD-A-PAK Generation VII Power Modules Thyristor/Diode and Thyristor/Thyristor, 45 A/60 A



ADD-A-PAK

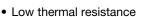
PRODUCT SUMMARY					
I _{T(AV)} or I _{F(AV)}	45 A/60 A				
Туре	Modules - Thyristor, Standard				

MECHANICAL DESCRIPTION

The ADD-A-PAK generation VII, new generation of ADD-A-PAK module, combines the excellent thermal performances obtained by the usage of exposed direct bonded copper substrate, with advanced compact simple package solution and simplified internal structure with minimized number of interfaces.

FEATURES

- · High voltage
- Industrial standard package



- UL approved file E78996
- Designed and qualified for industrial level
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Excellent thermal performances obtained by the usage of exposed direct bonded copper substrate
- Up to 1600 V
- · High surge capability
- Easy mounting on heatsink

ELECTRICAL DESCRIPTION

These modules are intended for general purpose high voltage applications such as high voltage regulated power supplies, lighting circuits, temperature and motor speed control circuits, UPS, and battery charger.

MAJOR RATIN	MAJOR RATINGS AND CHARACTERISTICS						
SYMBOL	CHARACTERISTICS	VSK.41	VSK.56	UNITS			
I _{T(AV)} or I _{F(AV)}	85 °C	45	60				
I _{O(RMS)}	As AC switch	100	135				
I _{TSM} ,	50 Hz	850	1200	A			
I _{FSM}	60 Hz	890	1256				
l ² t	50 Hz	3.61	7.20	kA ² s			
I-I	60 Hz	3.30	6.57	KA-S			
I ² √t		36.1	72	kA ² √s			
V_{RRM}	Range	400 to	1600	V			
T _{Stg}		-40 t	°C				
T _J		-40 t					



ELECTRICAL SPECIFICATIONS

VOLTAGE RA	ATINGS				
TYPE NUMBER	VOLTAGE CODE	V _{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM REPETITIVE PEAK OFF-STATE VOLTAGE, GATE OPEN CIRCUIT V	I _{RRM,} I _{DRM} AT 125 °C mA
	04	400	500	400	
	06	600	700	600	
VOK 41	08	800	900	800	
VSK.41 VSK.56	10	1000	1100	1000	15
VSIX.30	12	1200	1300	1200	
	14	1400	1500	1400	
	16	1600	1700	1600	

ON-STATE CONDUCTION							
PARAMETER	SYMBOL	1	EST CONDITION	ONS	VSK.41	VSK.56	UNITS
Maximum average on-state current (thyristors)	I _{T(AV)}	180° conduction, half sine wave,		45	60		
Maximum average forward current (diodes)	I _{F(AV)}	$T_C = 85 ^{\circ}C$			45	60	
Maximum continuous RMS on-state current, as AC switch	I _{O(RMS)}	•	(RMS) or	I _(RMS)	100	135	A
		t = 10 ms	No voltage	Sinusoidal	850	1200	
Maximum peak, one-cycle non-repetitive	I _{TSM}	t = 8.3 ms	reapplied	half wave,	890	1256	
on-state or forward current	or I _{FSM}	t = 10 ms	100 % V _{RRM}	initial T _J =	715	1000	
	1 3101	t = 8.3 ms	reapplied	T _J maximum	750	1056	.
Maximum I ² t for fusing		t = 10 ms	No voltage		3.61	7.20	kA ² s
	I ² t	t = 8.3 ms	reapplied	Initial $T_J = T_J$ maximum	3.30	6.57	
		t = 10 ms	100 % V _{RRM}		2.56	5.10	
		t = 8.3 ms	reapplied		2.33	4.56	
Maximum I ² √t for fusing	I ² √t ⁽¹⁾	t = 0.1 ms to 10 $T_J = T_J \text{ maximu}$		e reapplied	36.1	72	kA²√s
Maximum value or threshold voltage	V (2)	Low level (3)	T _ T mayin	aum	1.08	0.91	V
waximum value or threshold voltage	V _{T(TO)} (2)	High level (4)	$T_J = T_J \text{ maxin}$	num	1.12	1.02	V
Maximum value of on-state	r _t ⁽²⁾	Low level (3)	T T mayin		4.7	4.27	mΩ
slope resistance	It (=)	High level ⁽⁴⁾	$T_J = T_J$ maximum		4.5	3.77	1115.2
Maximum made on atota as familiard valtage	V_{TM} $I_{TM} = \pi$		T 05.00		1.81	1.7	V
Maximum peak on-state or forward voltage	V _{FM}	$I_{FM} = \pi \times I_{F(AV)}$ $T_{J} = 25 \text{ °C}$		1.01	1.7	V	
Maximum non-repetitive rate of rise of turned on current	dl/dt	$T_{J} = 25$ °C, from 0.67 V_{DRM} , $I_{TM} = \pi \times I_{T(AV)}$, $I_{g} = 500$ mA, $t_{r} < 0.5$ μ s, $t_{p} > 6$ μ s		1	50	A/µs	
Maximum holding current	I _H	$T_J = 25$ °C, anode supply = 6 V, resistive load, gate open circuit		00	mA		
Maximum latching current	ΙL	$T_J = 25$ °C, and	ode supply = 6 \	/, resistive load	400	400	

⁽¹⁾ I^2t for time $t_x = I^2\sqrt{t} \ x \ \sqrt{t_x}$

⁽²⁾ Average power = $V_{T(TO)} \times I_{T(AV)} + r_t \times (I_{T(RMS)})^2$ (3) 16.7 % x π x $I_{AV} < I < \pi$ x I_{AV}

 $^{^{(4)}~}I>\pi~x~I_{AV}$



TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS		VSK.41	VSK.56	UNITS
Maximum peak gate power	P_{GM}			1	0	W
Maximum average gate power	P _{G(AV)}			2	.5	VV
Maximum peak gate current	I _{GM}			2	.5	Α
Maximum peak negative gate voltage	- V _{GM}			1	0	
		T _J = -40 °C		4.0		V
Maximum gate voltage required to trigger	V_{GT}	T _J = 25 °C	Anode supply = 6 V resistive load	2	2.5	
		T _J = 125 °C		1.	.7	
		T _J = -40 °C		27	70	
Maximum gate current required to trigger	I _{GT}	T _J = 25 °C	Anode supply = 6 V resistive load	150		mA
		T _J = 125 °C	Tosistive load	8	0	
Maximum gate voltage that will not trigger	V_{GD}	T _J = 125 °C, rated V _{DRM} applied		0.:	25	V
Maximum gate current that will not trigger	I _{GD}	$T_J = 125$ °C, rated V_{DRM} applied 6		6	mA	

BLOCKING					
PARAMETER	SYMBOL	TEST CONDITIONS	VSK.41	VSK.56	UNITS
Maximum peak reverse and off-state leakage current at V _{RRM} , V _{DRM}	I _{RRM,} I _{DRM}	T _J = 125 °C, gate open circuit	1	5	mA
Maximum RMS insulation voltage V_{INS} 50 Hz $\frac{3000 (1)}{3600 (1)}$,	٧		
Maximum critical rate of rise of off-state voltage	dV/dt	T_J = 125 °C, linear to 0.67 V_{DRM}	10	00	V/µs

THERMAL AND MECHA	THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VSK.41 VSK.56		UNITS
Junction operating and storage temperature range		T _J , T _{Stg}		-40 to	o 125	°C
Maximum internal thermal resistation to case per leg	ance,	R _{thJC}	DC operation	0.44	0.35	°C/W
Typical thermal resistance, case to heatsink per module		R _{thCS}	Mounting surface flat, smooth and greased		0.1	
to heatsink			A mounting compound is recommended and the torque should be rechecked after a period of	4		Nm
Mounting torque ± 10 %	busbar		3 hours to allow for the spread of the compound.	3	3	INIII
Approximate weight				7	5	g
Approximate weight				2	.7	oz.
Case style			JEDEC®	AAP GE	N VII (TO-	-240AA)

AR CONDUCTION PER JUNCTION											
DEVICES		SINE HALF	WAVE CO	NDUCTIO	N	RE	CTANGUL	AR WAVE C	CONDUCTION	ON	LIMITE
DEVICES	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VSK.41	0.110	0.131	0.17	0.23	0.342	0.085	0.138	0.177	0.235	0.345	°C/W
VSK.56	0.088	0.104	0.134	0.184	0.273	0.07	0.111	0.143	0.189	0.275	C/VV

Note

Table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

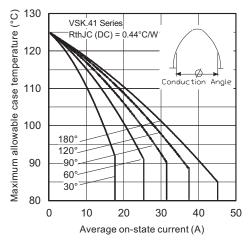


Fig. 1 - Current Ratings Characteristics

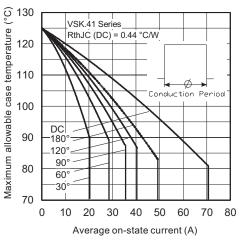


Fig. 2 - Current Ratings Characteristics

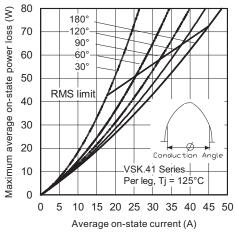


Fig. 3 - On-State Power Loss Characteristics

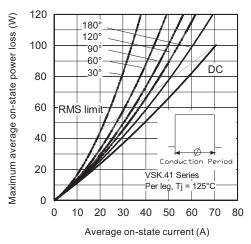
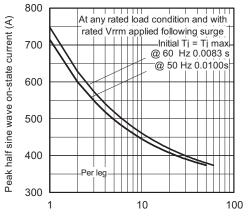


Fig. 4 - On-State Power Loss Characteristics



Number of equal amplitude half cycle current pulses (N)

Fig. 5 - Maximum Non-Repetitive Surge Current

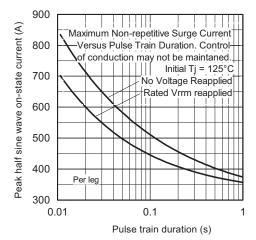


Fig. 6 - Maximum Non-Repetitive Surge Current

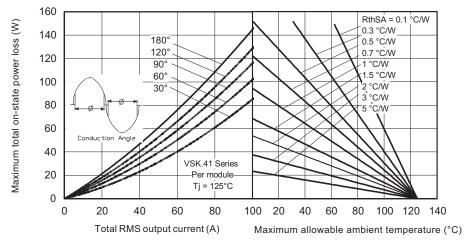


Fig. 7 - On-State Power Loss Characteristics

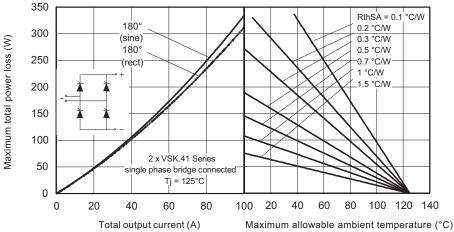


Fig. 8 - On-State Power Loss Characteristics

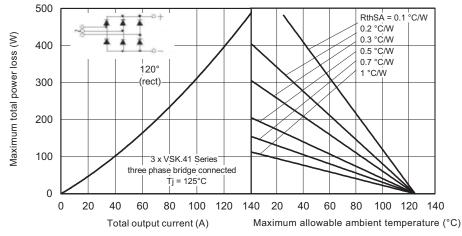


Fig. 9 - On-State Power Loss Characteristics

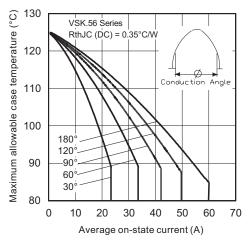


Fig. 10 - Current Ratings Characteristics

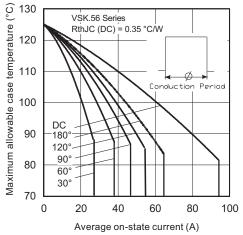


Fig. 11 - Current Ratings Characteristics

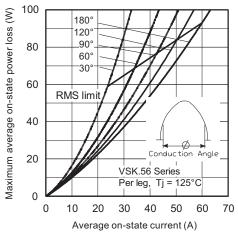


Fig. 12 - On-State Power Loss Characteristics

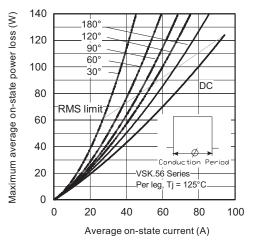
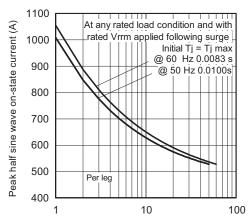


Fig. 13 - On-State Power Loss Characteristics



Number of equal amplitude half cycle current pulses (N)

Fig. 14 - Maximum Non-Repetitive Surge Current

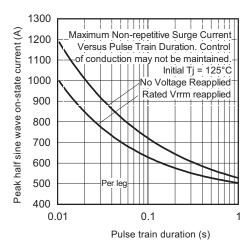


Fig. 15 - Maximum Non-Repetitive Surge Current

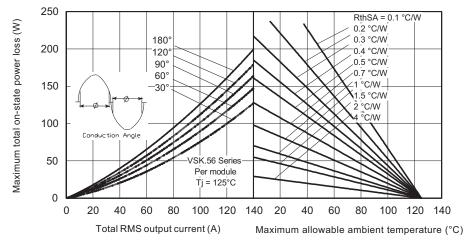


Fig. 16 - On-State Power Loss Characteristics

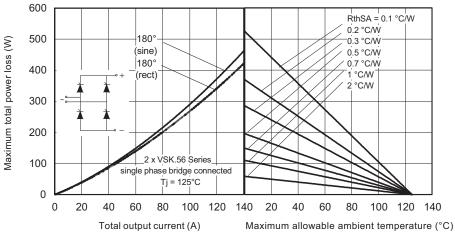


Fig. 17 - On-State Power Loss Characteristics

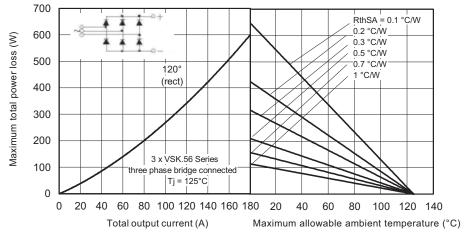


Fig. 18 - On-State Power Loss Characteristics

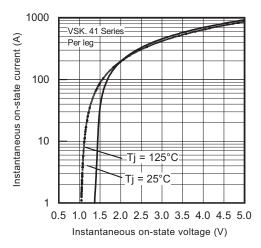


Fig. 19 - On-State Voltage Drop Characteristics

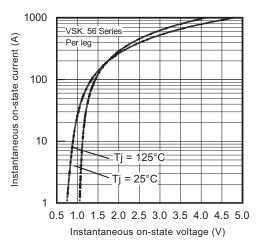


Fig. 20 - On-State Voltage Drop Characteristics

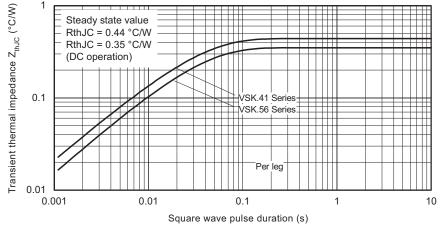


Fig. 21 - Thermal Impedance Z_{thJC} Characteristics

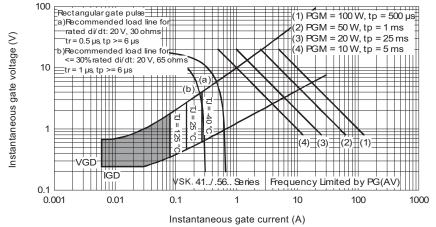
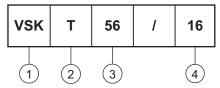


Fig. 22 - Gate Characteristics



ORDERING INFORMATION TABLE





1 - Module type

Circuit configuration (see end of datasheet)

3 - Current code 41 = 45 A 56 = 60 A

4 - Voltage code (see Voltage Ratings table)

Note

To order the optional hardware go to <u>www.vishay.com/doc?95172</u>

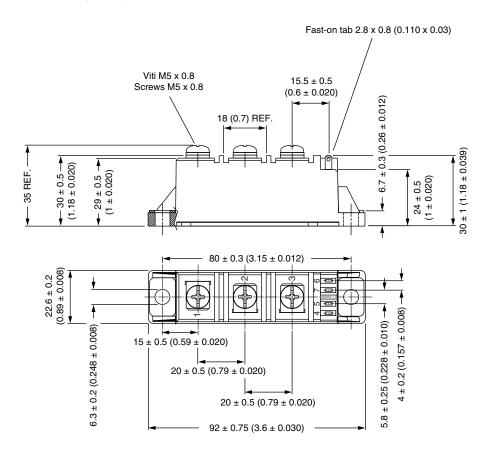
CIRCUIT CONFIGURATION		
CIRCUIT DESCRIPTION	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING
Two SCRs doubler circuit	Т	VSKT 1 (2) (2) (2) (2) (3) (3) (4) (5) (7) (6)
SCR/diode doubler circuit, positive control	н	VSKH 1 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2
SCR/diode doubler circuit, negative control	L	VSKL 1
SCR/diode common anodes	N	VSKN (1) (1) (2) (3) (3) (4) (5) (4) (5)

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95368			



ADD-A-PAK Generation VII - Thyristor

DIMENSIONS in millimeters (inches)





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Revision: 02-Oct-12 Document Number: 91000

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TD92N16KOF-A TT250N12KOF-K VS-2N692 VS-2N689 VS-25RIA40 VS-16RIA120 VS-10RIA120 VS-30TPS08PBF NTE5427
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